

S2AF THRU S2MF

Surface Mount General Purpose Silicon Rectifiers

Reverse Voltage - 50 to 1000 V

Forward Current - 2 A

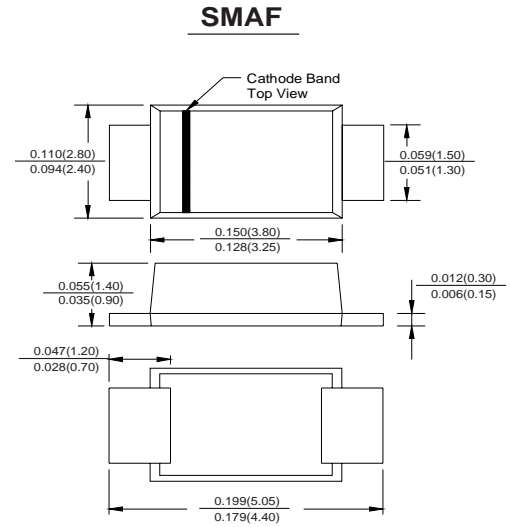


FEATURES

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Easy to pick and place
- Lead free in comply with EU RoHS 2011/65/EU directives

MECHANICAL DATA

- Case: SMAF
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 27mg 0.00086oz



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	S2AF	S2BF	S2DF	S2GF	S2JF	S2KF	S2MF	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at $T_a = 65\text{ }^\circ\text{C}$	$I_{F(AV)}$	2							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	60							A
Maximum Instantaneous Forward Voltage at 2 A	V_F	1.1							V
Maximum DC Reverse Current at Rated DC Blocking Voltage $T_a = 25\text{ }^\circ\text{C}$ $T_a = 125\text{ }^\circ\text{C}$	I_R	1 125							μA
Typical Junction Capacitance ¹⁾	C_j	30							pF
Typical Thermal Resistance ²⁾	$R_{\theta JA}$	16							$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150							$^\circ\text{C}$

1) Measured at 1 MHz and applied reverse voltage of 4 V D.C

2) Thermal resistance from junction to ambient at 0.375" (9.5 mm) lead length, P.C.B. mounted



Fig.1 Forward Current Derating Curve

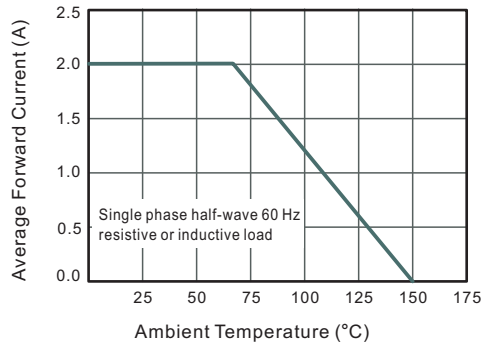


Fig.2 Typical Instaneous Reverse Characteristics

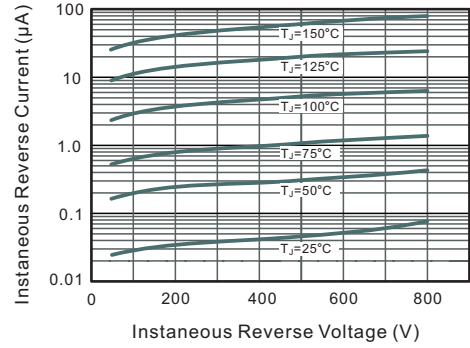


Fig.3 Typical Forward Characteristic

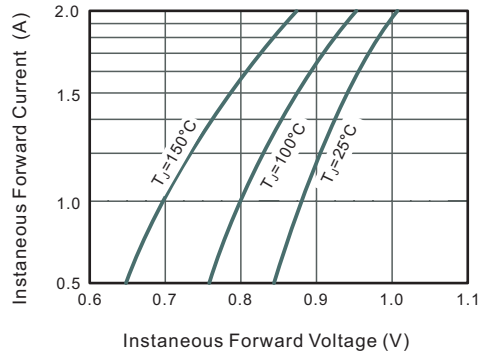


Fig.4 Typical Junction Capacitance

